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ABSTRACT OF THE DISCLOSURE

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Structures and methods for making a magnetic structure are discussed. Various embodiments increase a magnetic field to unambiguously select a magnetic memory cell structure. One method includes folding a current line into two portions around a magnetic memory cell structure. Each portion contributes its magnetic flux to increase the magnetic field to unambiguously select the magnetic memory cell structure. Another method increases the flux density by reducing a cross-sectional area of a portion of the current line, wherein the portion of the current line is adjacent to the to the magnetic memory cell structure.

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